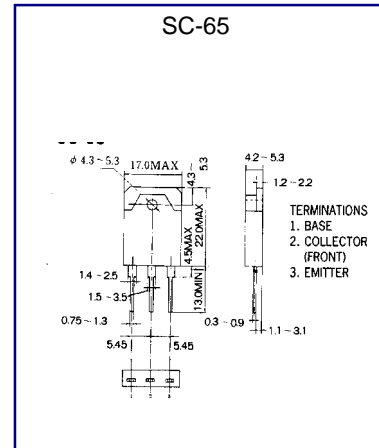




BUT56A

NPN EPITAXIAL SILICON TRANSISTOR

**HIGH VOLTAGE SWITCHING USE IN
HORIZONTAL DEFLECTION OUTPUT STAGE**



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------------|--------|---------|------|
| Collector-Base Voltage | VCBO | 1000 | V |
| Collector-Emitter Voltage | VCEO | 450 | V |
| Emitter-Base voltage | VEBO | 6 | V |
| Collector Current (DC) | IC | 8 | A |
| Collector Peak Current | ICM | 10 | A |
| Base Current (DC) | IB | 4 | A |
| Collector Dissipation (Tc=25°C) | PC | 100 | W |
| Junction Temperature | Tj | 150 | °C |
| Storage Temperature | Tstg | -65~150 | °C |

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|--------------------------------------|----------|---------------------|-----|-----|------|------|
| Collector Cutoff Current (VBE=0) | ICES | VCE= 800V , VEB= 0 | | | 5 | mA |
| Emitter Cutoff Current(IC=0) | IEBO | VEB= 6V , IC=0 | | | 1 | mA |
| Collector Emitter Saturation Voltage | VCE(sat) | IC=5A, IB=0.5A | | | 2.5 | V |
| Base- Emitter Saturation Voltage | VBE(sat) | IC=5A, IB=1.2A | | | 2.5 | V |
| Current Gain Bandwidth Product | fT | VCE= 10V , IC=500mA | 10 | | | MHZ |
| Turn-Off Time | toff | IC=4A, IB=0.4A | | | 0.75 | μS |
| | | IC=4A, IB=0.6A | | | 0.5 | μS |
| | | IC=5A, IB=1.0A | | | 0.5 | μS |